

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	3283	ammonium adj fluoride and hydrochloric adj acid	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 14:30
S2	714	etching and S1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 09:16
S3	468	semiconductor and S2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 09:25
S4	19297	silicon adj oxide adj layer and "4"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 09:25
S5	19297	silicon adj oxide adj layer and S4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 09:25
S6	37	silicon adj oxide adj layer and S3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 10:38
S7	2	("4759823").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/23 10:35
S8	2	("5350448").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/23 10:35

S9	2	("5445979").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/23 10:35
S10	2	("3777227").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/23 10:35
S11	2	("5256247").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/23 10:36
S12	2	("5402807").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/23 10:36
S13	2	("5828129").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/23 10:36
S14	2	("5587046").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/23 10:36
S15	3	("3911613").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/23 10:37
S16	3283	ammonium adj fluoride and hydrochloric adj acid	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 10:38

S17	714	etching and S16	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 10:38
S18	468	semiconductor and S17	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 10:38
S19	37	silicon adj oxide adj layer and S18	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 10:38
S20	34	S19 and device	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 10:40
S21	500	device and etching and ammonium adj fluoride and hydrochloric adj acid	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 10:41
S22	34	S20	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 10:41
S23	34	S20 and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 10:57
S24	1005	device and titanium adj layer and silicon adj layer and etching	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 11:01

S25	37162	S24 and ammonium fluoride and hydrochloric adj acid	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 10:59
S26	3	S24 and ammonium adj fluoride and hydrochloric adj acid	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 10:59
S27	3283	ammonium adj fluoride and hydrochloric adj acid	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 11:01
S28	300	S27 and semiconductor adj device	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 11:02
S29	268	S28 and etching	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 11:04
S30	268	S29 and device	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 11:05
S31	1810896	su "391613"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 11:06
S32	3	"391613".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 11:06

S33	0	silicon adj oxide adj layer and titant adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 11:53
S34	5669	silicon adj oxide and titanate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 13:31
S35	1875	"2" and (batio or srtio or basrtio)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 12:50
S36	1875	S35 and (batio or srtio or basrtio)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 12:50
S37	3	"6620738"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 12:50
S38	8	("3777227" "4759823" "5256247" "5350448" "5402807" "5445979" "5587046" "5828129").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/23 12:50
S39	331	pzt and silicon adj oxide adj layer and titanate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 12:51
S40	869	silicon adj oxide adj layer and titanate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 12:51
S41	2	silicon adj oxide adj layer and titanante near3 layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 12:53

S42	25	"6291319"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 12:53
S43	2	"6291319".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 12:53
S44	9	("5208182" "5225031" "5393352" "5450812" "5482003" "5514484" "5830270" "5907792" "6224669").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/08/23 12:53
S45	3733906	etched adj silicon layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 13:31
S46	230	etched adj silicon adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 13:32
S47	3	etched adj titanium adj layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 13:33
S48	9	titanium adj layer adj etching	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 13:34
S49	0	(batio3 or srtio3) adj layer adj etching	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 13:34
S50	2	"5326721".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/23 14:30